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I-V characteristic analysis of InSe/ZnO/Au and GaAs/Al₂O₃/Au thin film FET coated using pulsed laser deposition

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The characteristics of InSe/ZnO/Au and GaAs/Al₂O₃/Au thin film FET such as structural, optical, surface morphology and electrical properties are focused in this research. The target materials are deposited on silicon substrate and glass substrate layer by layer using Physical Vapor Deposition (PVD) preceded by Pulsed Laser Deposition technique (PLD) and the final layer was coated using sputtering instrument. Investigation of parameters that alters the property of thin film FET was carried out. The parameters such as temperature, film thickness and oxygen pressure during the deposition contribute the change in property of the thin film FET. The structural property of thin film FET is studied using X-ray diffraction (XRD). The optical properties were characterised using UV-Vis-NIR spectrophotometer. The surface morphology is determined by Scanning Electron Microscopy (SEM). IV characterization of InSe/ZnO/Au and GaAs/Al₂O₃/Au thin film FET was done.

Biography

Persis Preethi is in her research area based on nanotechnology since two years as she is still pursuing her education and would like to research on new emerging trends in nanotechnology. She has the touch of research work in Nanobiotechnology, Nanophysics.

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